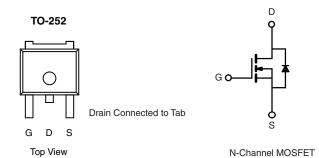


Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	60				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0076				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.009				
I _D (A)	50				
Configuration	Single				



FEATURES

 Halogen-free According to IEC 61249-2-21 Definition



- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- 100 % R_g and UIS Tested
- AEC-Q101 Qualifiedd
- Compliant to RoHS Directive 2002/95/EC

ROHS COMPLIANT HALOGEN FREE

ORDERING INFORMATION				
Package	TO-252			
Lead (Pb)-free and Halogen-free	SQD50N06-07L-GE3			

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unles		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	60	V
Gate-Source Voltage		V _{GS}	± 20	V
Continuous Drain Current ^a	T _C = 25 °C	1	50	
	T _C = 125 °C	I _D	50	
Continuous Source Current (Diode Conduction) ^a		I _S	50	А
Pulsed Drain Current ^b		I _{DM}	200	
Single Pulse Avalanche Current	0.111	I _{AS}	48	
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	115	mJ
Martin as Barras Biratas Barba	T _C = 25 °C	Б	136	10/
Maximum Power Dissipation ^b	T _C = 125 °C	P_{D}	45	W
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	50	°C/W
Junction-to-Case (Drain)		R_{thJC}	1.1	C/ VV

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



SQD50N06-07L Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static							,	
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		60	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = 250 \mu A$		2.0	2.5	V	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 60 V	-	-	1.0		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μΑ	
		$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 175 °C	-	-	250		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α	
		V _{GS} = 10 V	I _D = 20 A	-	0.0064	0.0076	Ω	
Drain Sauras On State Besistance	В	V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.0130		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.0160		
		V _{GS} = 4.5 V	I _D = 20 A	-	0.0078	0.0090		
Forward Transconductanceb	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		-	82	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}			-	4455	5570		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{GS} = 0 V V _{DS} = 25 V, f = 1 MHz		407	510	рF	
Reverse Transfer Capacitance	C _{rss}			-	223	280		
Total Gate Charge ^c	Qg			-	80	120		
Gate-Source Charge ^c	Q_{gs}	V _{GS} = 10 V	$V_{DS} = 30 \text{ V}, I_{D} = 50 \text{ A}$	-	11.1	-	nC	
Gate-Drain Charge ^c	Q_{gd}				15.7	-	1	
Gate Resistance	R_{g}	f = 1 MHz		1	2	3	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	12	18		
Rise Time ^c	t _r	$V_{DD} = 30 \text{ V}, \text{ R}_L = 0.6 \Omega$ $I_D \cong 50 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		-	13	20	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	42	63		
Fall Time ^c	t _f			-	7	11		
Source-Drain Diode Ratings and Chara	acteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	200	Α	
Forward Voltage	V_{SD}	I _F = 20 A, V _{GS} = 0 V		-	0.85	1.5	V	

Notes

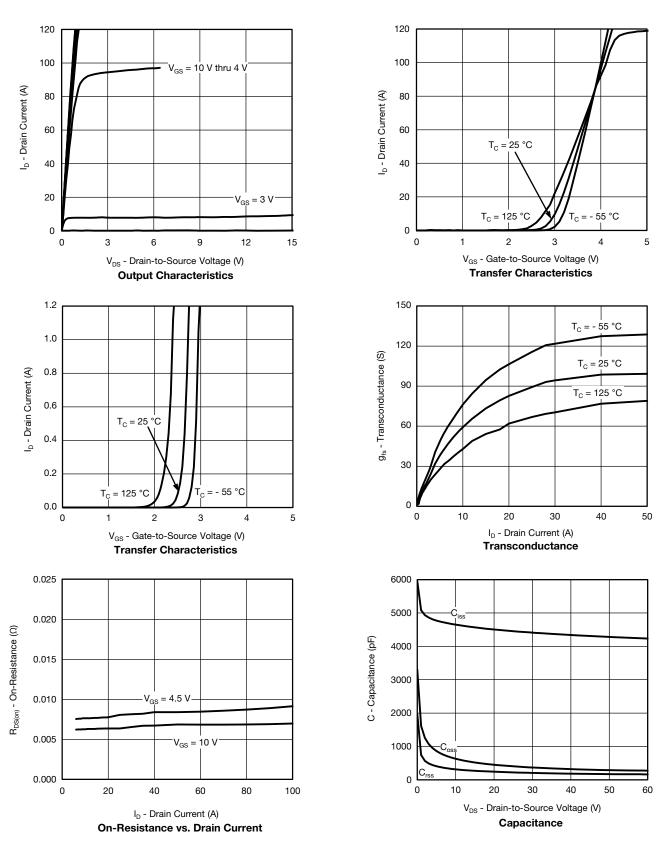
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



Automotive N-Channel 60 V (D-S) 175 °C MOSFET

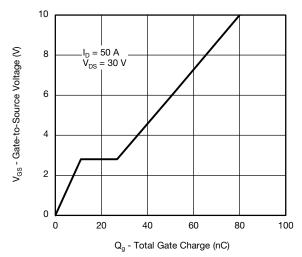
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



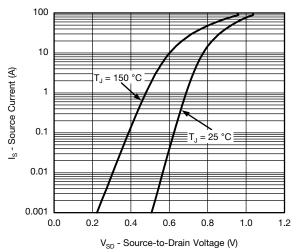


Automotive N-Channel 60 V (D-S) 175 °C MOSFET

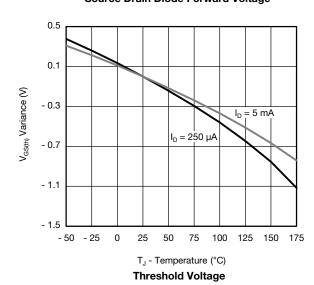
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

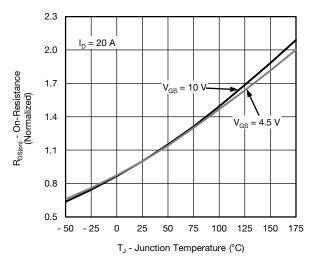


Gate Charge

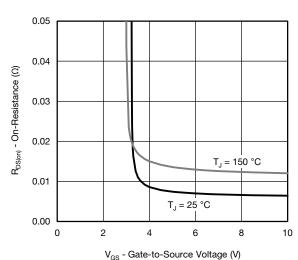


Source Drain Diode Forward Voltage

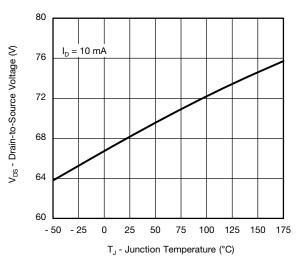




On-Resistance vs. Junction Temperature



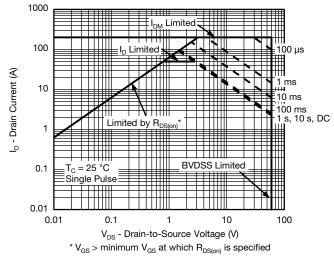
On-Resistance vs. Gate-to-Source Voltage



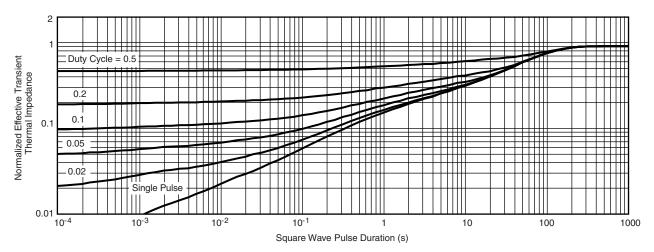
Drain Source Breakdown vs. Junction Temperature

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Safe Operating Area

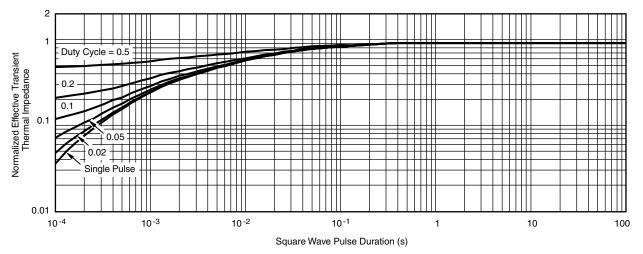


Normalized Thermal Transient Impedance, Junction-to-Ambient

SQD50N06-07L Automotive N-Channel

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

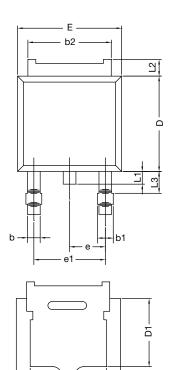
Note

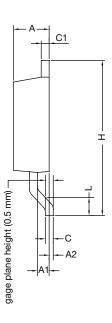
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

TO-252AA CASE OUTLINE





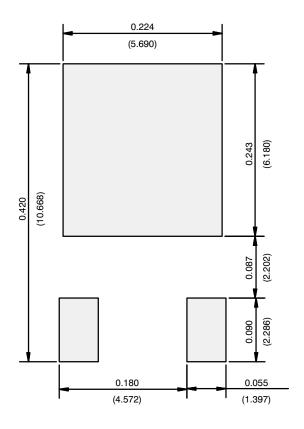
	MILLIN	IETERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
A2	0.030	0.127	0.001	0.005	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.10	4.45	0.161	0.175	
Е	6.48	6.73	0.255	0.265	
E1	4.49	5.50	0.177	0.217	
е	2.28	BSC	0.090 BSC		
e1	4.57	BSC	0.180 BSC		
т	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	0.64	1.02	0.025	0.040	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347					

Note

• Dimension L3 is for reference only.

SQD50N06-07L Automotive N-Channel 60 V (D-S) 175 °C MOSFET

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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SQD50N06-07L Automotive N-Channel 60 V (D-S) 175 °C MOSFET

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